Schottky barrier diode

RB521S–30 *New*

●Applications

Low current rectification and high speed switching

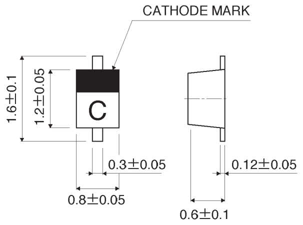
●Features

1) Small surface mounting type.(EMD2)
2) High rectifying current of 200 mA with the small package.
3) Low reverse current and low forward voltage.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



ROHM : EMD2
EIAJ : SC-79
JEDEC : SOD-523

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	200	mA
Peak forward surge current∗	I_{FSM}	1	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−55～+125	℃

∗ 60 Hz for 1 ∿

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	−	0.40	0.50	V	I_F=200mA
Reverse current	I_R	−	4.0	30	μA	V_R=10V

∗ ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

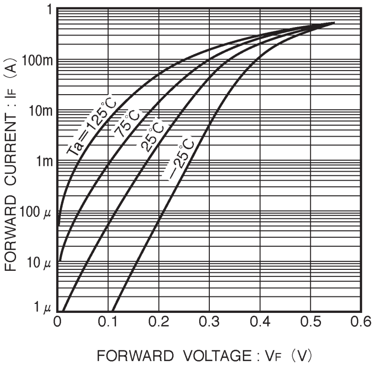


Fig. 1 Forward characteristics

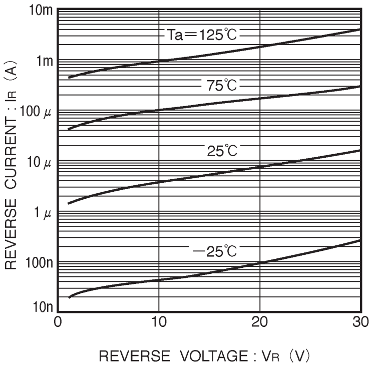


Fig. 2 Reverse characteristics

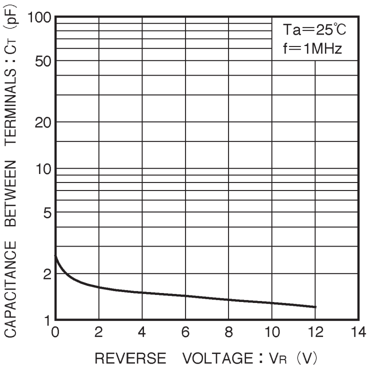


Fig. 3 Capacitance between terminals characteristics

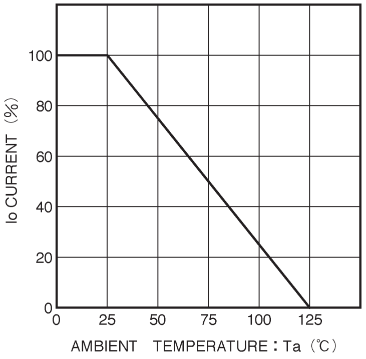


Fig. 4 Derating curve (mounting on glass epoxy PCBs)